ABSTRACT OF THE DISCLOSURE

The present invention relates to a method for the production of semiconductor components. This method comprises the steps applying masking layers and components on epitaxial semiconductor substrates within the epitaxy reactor without removal of the substrate from the reactor. The masking layers may be HF soluble such that a gas etchant may be introduced within the reactor so as to etch a select number and portion of masking layers. This method may be used for production of lateral integrated components on a substrate wherein the components may be of the same or different type. Such types include electronic and optoelectronic components. Numerous masking layers may be applied, each defining particular windows intended to receive each of the various components. In the reactor, the masks may be selectively removed, then the components grown in the newly exposed windows.